

NCE N-Channel Enhancement Mode Power MOSFET

Description

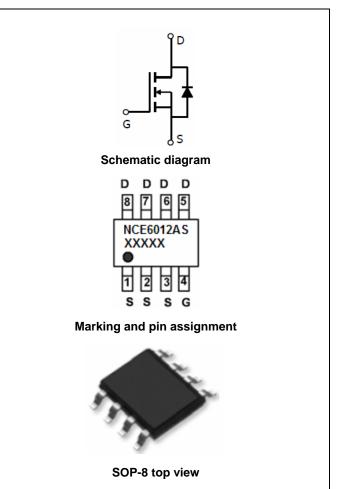
The NCE6012AS uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = 60V, I_D = 12A$ $R_{DS(ON)} < 11m\Omega @ V_{GS} = 10V$ (Typ:8.5m Ω) $R_{DS(ON)} < 12m\Omega @ V_{GS} = 4.5V$ (Typ:9.1m Ω)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Low gate to drain charge to reduce switching losses

Application

- Power switching application
- Load switch



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE6012AS	NCE6012AS	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings (T_c=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	60	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	12	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	8.5	A
Pulsed Drain Current	I _{DM}	30	A
Maximum Power Dissipation	PD	3	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{θJA}	42	°C /W	
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Electrical Characteristics (TC=25°C unless otherwise noted)

Parameter	Parameter Symbol Condition		Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.9	1.3	1.8	V
Drain Course On Chate Desintance	D	V_{GS} =10V, I_{D} =12A	-	8.5	11	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =4.5V, I_D =6A	-	9.1	12	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =12A	40	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	4100	-	PF
Output Capacitance	Coss	V _{DS} =30V,V _{GS} =0V, F=1.0MHz	-	298	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHZ	-	229	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	8.5	-	nS
Turn-on Rise Time	tr	V_{DD} =30V, R _L =1 Ω	-	7	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =3 Ω	-	40	-	nS
Turn-Off Fall Time	t _f		-	15	-	nS
Total Gate Charge	Qg		-	93	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=30V, I_{D}=12A,$	-	9.7	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	20	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =12A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	12	А
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =12A	-	32	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	45	-	nC
	1					

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^{\circ}$ C. The value in any given application depends on the user's specific board design.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

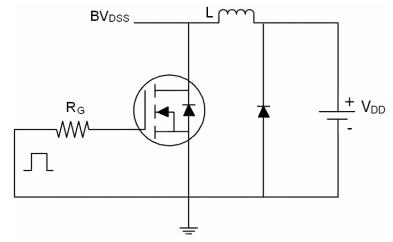
4. Guaranteed by design, not subject to production



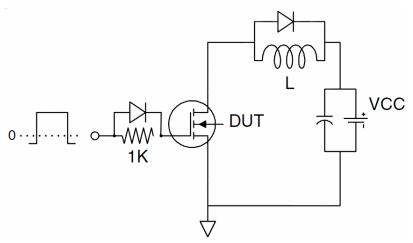
http://www.ncepower.com

Test Circuit

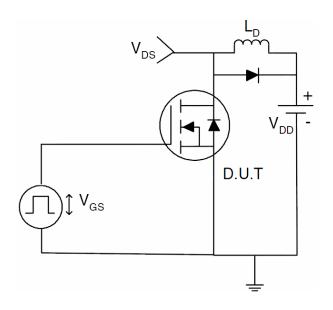
1) E_{AS} test Circuit



2) Gate charge test Circuit

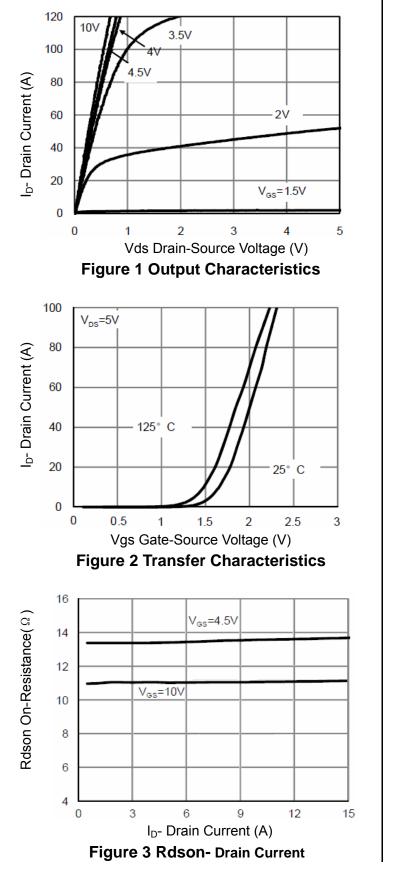


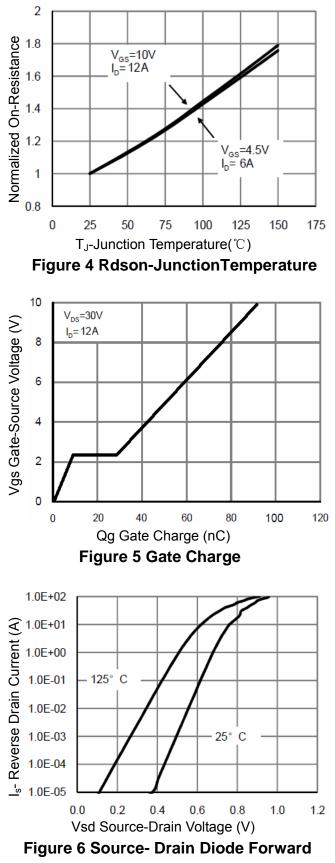
3) Switch Time Test Circuit





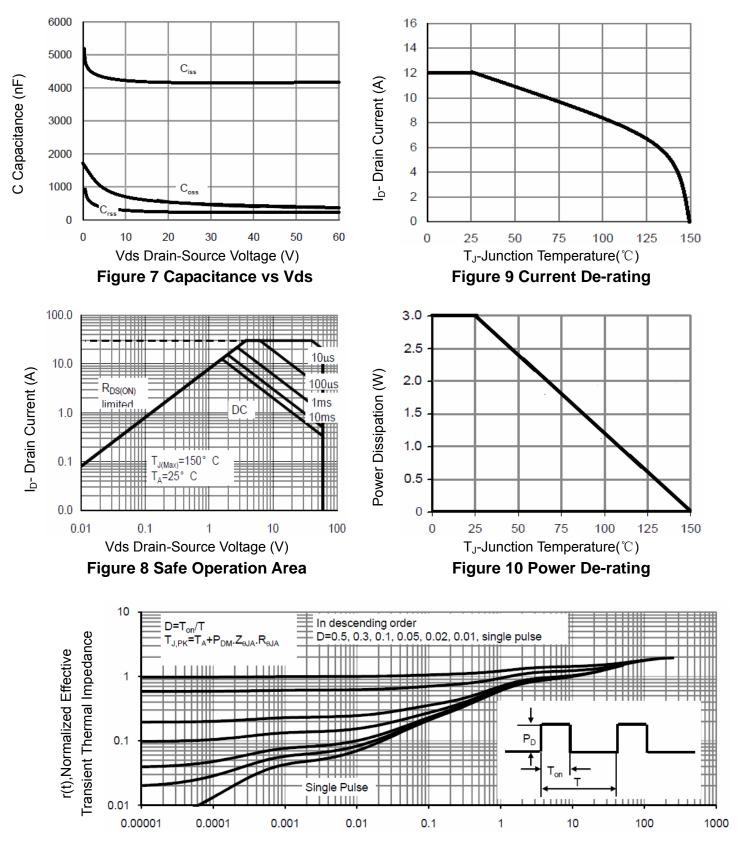
Typical Electrical and Thermal Characteristics (Curves)







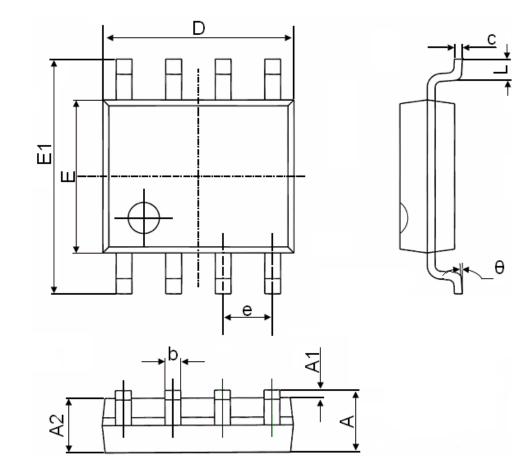
http://www.ncepower.com



Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



Symbol	Dimensions	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
e	1.270	(BSC)	0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

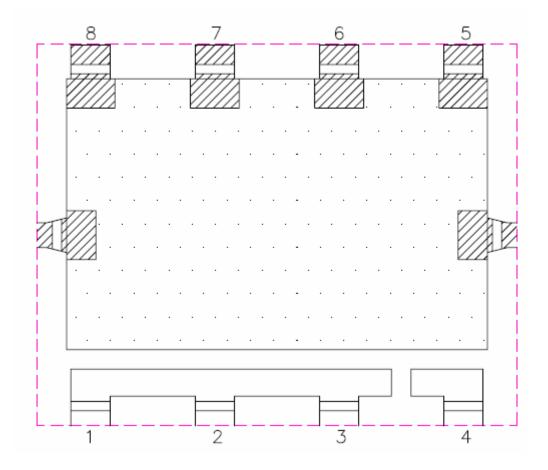


主材清单

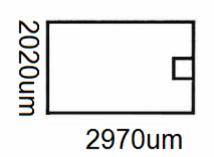
构成部品名 Name	构成部品供应 商名称(2nd) Supplier(2nd)	均质材质名 (原资材) Homogeneous materials	均质材质供应商名称(3rd) Supplier(3rd)		
		Lead Frame (A194)	ASM		
部品型号	部品制造商	Ероху (8062Т)	ABLESTIK		
		Mold Compound (CEL-8240HF10GK)	日立化成工业(苏州)有限公司		
		Wire	贺利氏招远 ; 韩国喜尚		
		Wire	韩国喜尚 日本 NMC		
		Sn	云南锡业		



框架示意图



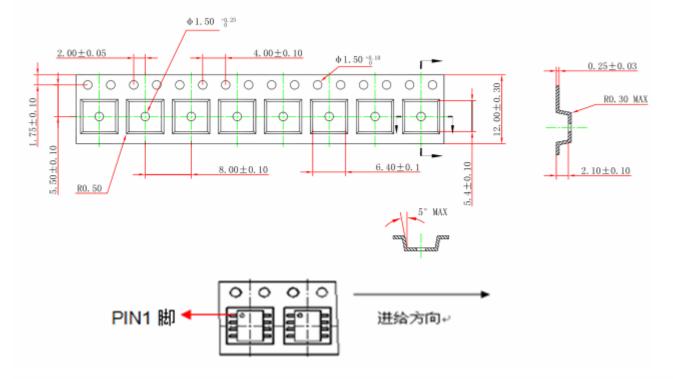
晶圆尺寸





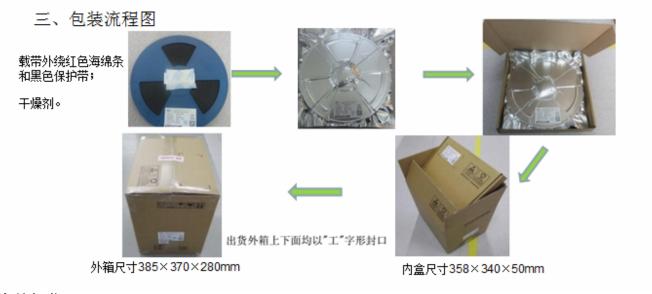
包装信息

一、载带图纸与产品搭载方向示意图:



二、包装信息表(满箱信息)

封装形式	包装方式	盘尺寸	只盘	盘内盒	只内盒	内盒箱	只箱
SOP8	编带	13 寸	4000	1	4000	5	20000



存储规范

NCE6012AS SOP-8 温湿度敏感等级三级



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